Amendments to the Claims

1. (withdrawn) A semiconductor switching device comprising:

a body of semiconductor material including a first major surface;

a first pair of current carrying electrodes formed in the first major surface;

a second pair of current carrying electrodes formed in the first major surface; and

a split control electrode structure including a first control electrode formed on the body of semiconductor material for controlling the first pair of current carrying electrodes, and a second control electrode formed on the body of semiconductor material for controlling the second pair of current carrying electrodes.

2. (withdrawn) The device of claim 1 wherein the split control electrode structure comprises a plurality of first control electrodes and a plurality of second control electrodes, wherein at least one second control electrode is interdigitated between a pair of first control electrodes.

3. (withdrawn) The device of claim 1 wherein the split control electrode structure comprises a plurality of first control electrodes and a plurality of second control electrodes, wherein more than one second control electrode is interdigitated between a pair of first control electrodes

4. (withdrawn) The device of claim 1 wherein the split control electrode structure comprises a plurality of first control electrodes and a plurality of second control electrodes, wherein

at least one second control electrode is juxtaposed to at least one first control electrode.

5. (withdrawn) The device of claim 1 wherein the first pair of current carrying electrodes comprises a first source region and a first drain region, and wherein the second pair of current carrying electrodes comprises a second source region and a second drain region, and wherein the first and second source regions are coupled together with a first electrode, and wherein the first and second drain regions are coupled together with second electrode.

6. (withdrawn) The device of claim 1 further comprising a current limit device coupled to the first and second control electrodes.

7. (withdrawn) The device of claim 1 further comprising a comparator device for turning on the second control electrode.

8. (withdrawn) The device of claim 1 wherein the first pair of current carrying electrodes comprise a first drain region and a first source region, and wherein the second pair of current carrying electrodes comprise a second drain region and second source region.

9. (withdrawn) The device of claim 8 wherein the first drain region and the second drain region form a common region within the body of semiconductor material.

10. (previously presented) A hot swap protection device comprising:

a split gate switching device including a first MOSFET device having a first gate electrode and a second MOSFET device having a second gate electrode;

a current limit device coupled to the first gate electrode for controlling the first MOSFET device during a current limit mode of operation; and

a comparator device coupled to the first and second gate electrodes for turning on the second MOSFET device during non-current limit mode of operation.

11. (original) The device of claim 10 wherein the split gate switching comprises:

a plurality of first gate electrodes for controlling a plurality of first MOSFET devices; and

a plurality of second gate electrodes for controlling a plurality of second MOSFET devices, wherein at least one second gate electrode is interdigitated between a pair of first gate electrodes.

12. (original) The device of claim 10 further comprising a load device coupled to drain regions of the first and second MOSFET devices.

13. (original) The device of claim 12 wherein the load device comprises a DC/DC converter.

14. (original) The device of claim 10 wherein the first and second MOSFET devices are formed in one body of semiconductor

material.

15. (original) The device of claim 10 wherein the first and second MOSFET devices, the current limit device, and the comparator device are formed on one body of semiconductor material.

16. (original) The device of claim 10 wherein the first MOSFET device forms an inrush current limit device.

Claims 17-20 (canceled).

21. (previously presented) A power switching structure comprising:

a split gate switching device including a first switch having a first control electrode and a second switch having a second control electrode;

a current limit device coupled to the first control electrode for controlling the first switch during a current limit mode of operation; and

a comparator device coupled to the second control electrode for turning on the second switch during a non-current limit mode of operation.

22. (previously presented) The structure of claim 21 further comprising a load device coupled to the first and second switches.

23. (previously presented) The structure of claim 21 wherein the first and second switches are formed in one body of semiconductor material.

24. (previously presented) The structure of claim 21 wherein the first and second switches, the current limit device, and the comparator device are formed on one body of semiconductor material.